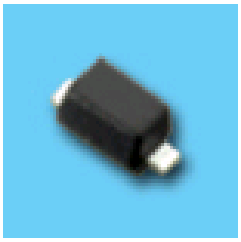
T-E5YA Low-capacitance bidirectional micro-packaged TVS Diodes for ESD Protection

The T-E5YA is designed with Tech chip Punch-Through process TVS technology to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space comes at a premium. Also because of its low capacitance, it is suited for use in high frequency designs such as USB 2.0 high speed, VGA, DVI, SDI and other high speed line applications.

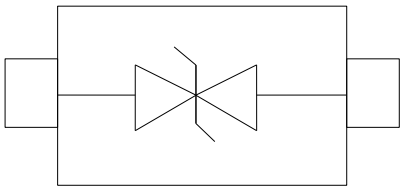
This series has been specifically designed to protect sensitive components which are connected to data and transmission lines from overvoltage caused by ESD(electrostatic discharge), and EFT (electrical fast transients).

Features

- Peak Power Dissipation – 80 W (8 x 20 us Waveform)
- Stand-off Voltage: 5.0 V
- Replacement for MLV (0603)
- Protects I/O Port
- Low Clamping Voltage
- Low Leakage
- Low Capacitance
- Low Body Height: 1.68mg
- Low capacitance (<6.0pF) for high-speed interfaces
- No insertion loss to 1.0GHz
- Response Time is < 1 ns
- Meets MSL 1 Requirements
- ROHS compliant
- **Solid-state Punch-Through TVS Process technology**
- Tech chip technology



SOD-523



Main applications

- High Speed Line :USB1.0/2.0, VGA, DVI, SDI,
- Serial and Parallel Ports
- Notebooks, Desktops, Servers
- Projection TV
- Cellular handsets and accessories
- Portable instrumentation
- Peripherals
-

Protection solution to meet

- IEC61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
- IEC61000-4-4 (EFT) 40A (5/50ns)

Ordering Information

Device	Qty per Reel	Reel Size
T-E5YA	3000	7 Inch

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Maximum ratings (Tamb=25℃ Unless Otherwise Specified)

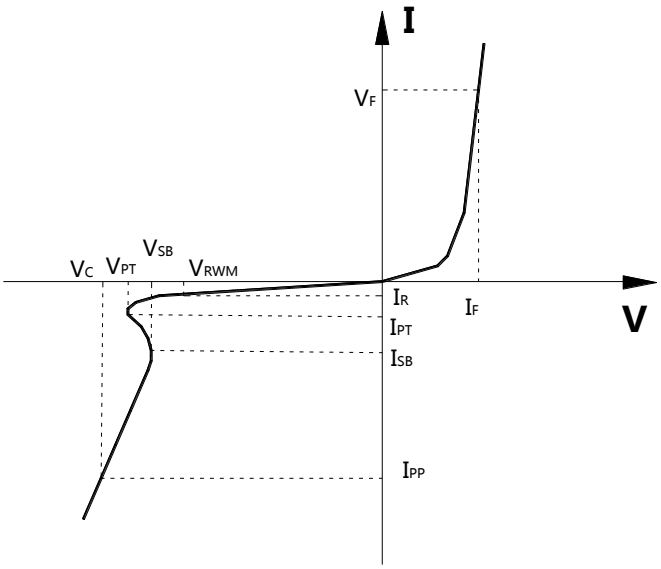
Parameter	Symbol	Value	Unit
Peak Pulse Power (tp=8/20μs waveform)	P_{PPP}	80	Watts
ESD Rating per IEC61000-4-2: Contact Air		8 15	KV
Lead Soldering Temperature	T_L	260 (10 sec.)	℃
Operating Temperature Range	T_J	-55 ~ 150	℃
Storage Temperature Range	T_{STG}	-55 ~ 150	℃
Lead Solder Temperature − Maximum (10 Second Duration)	T_L	260	℃

Electrical characteristics (Tamb=25℃ Unless Otherwise Specified)

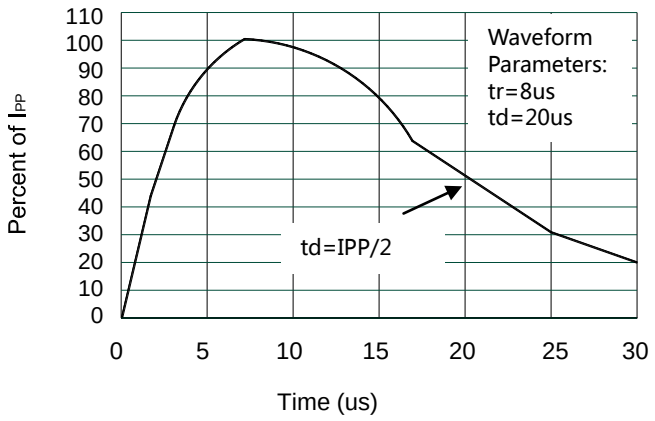
Device	V_{RWM}	I_R @ V_{RWM}	V_{PT} @ 1 mA	V_{SB} @ 50 mA	V_C	Capacitance	
			(Volts)	(Volts)	@ 1 A	@ V_R = 0 V, 1 MHz (pF)	
	(V)	(uA)	Min	Min	(V)	Typ	Max
T-E5YA	5.0	2	6.0	5.3	9.0	4.5	6

Junction capacitance is measured in VR=0V,F=1MHz

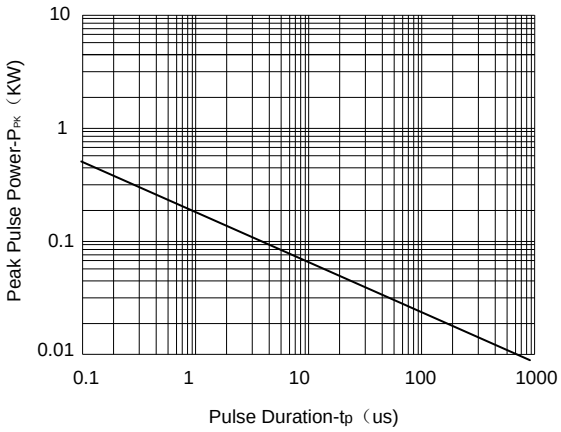
Symbol	Parameter
V_{RWM}	Working Peak Reverse Voltage
V_{PT}	Punch-Through Voltage@ I_{PT}
V_{SB}	Snap-Back Voltage@ I_{SB}
V_C	Clamping Voltage @ I_{PP}
I_T	Test Current
I_{RM}	Leakage current at V_{RWM}
I_{PP}	Peak pulse current
C_O	Off-state Capacitance
C_J	Junction Capacitance



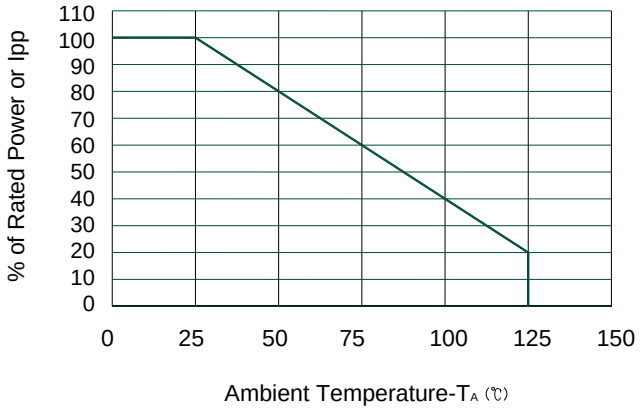
Typical electrical characterist applications



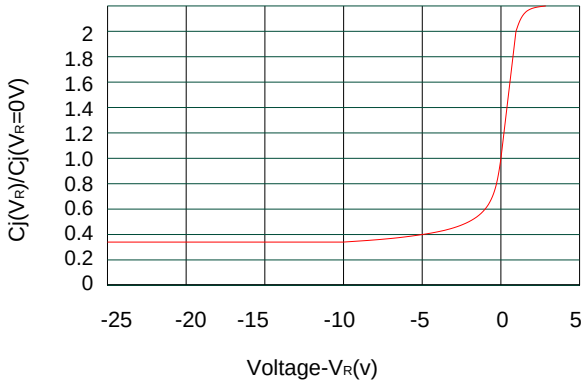
Pulse Waveform



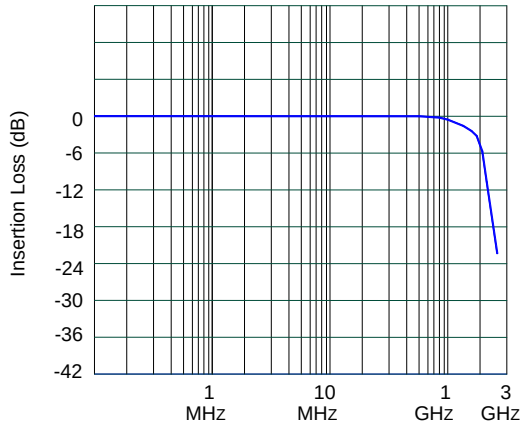
Non-Repetitive Peak Pulse Power vs. Pulse Time



Power Derating Curve



Junction Capacitance vs. Reverse Voltage



Insertion Loss S21

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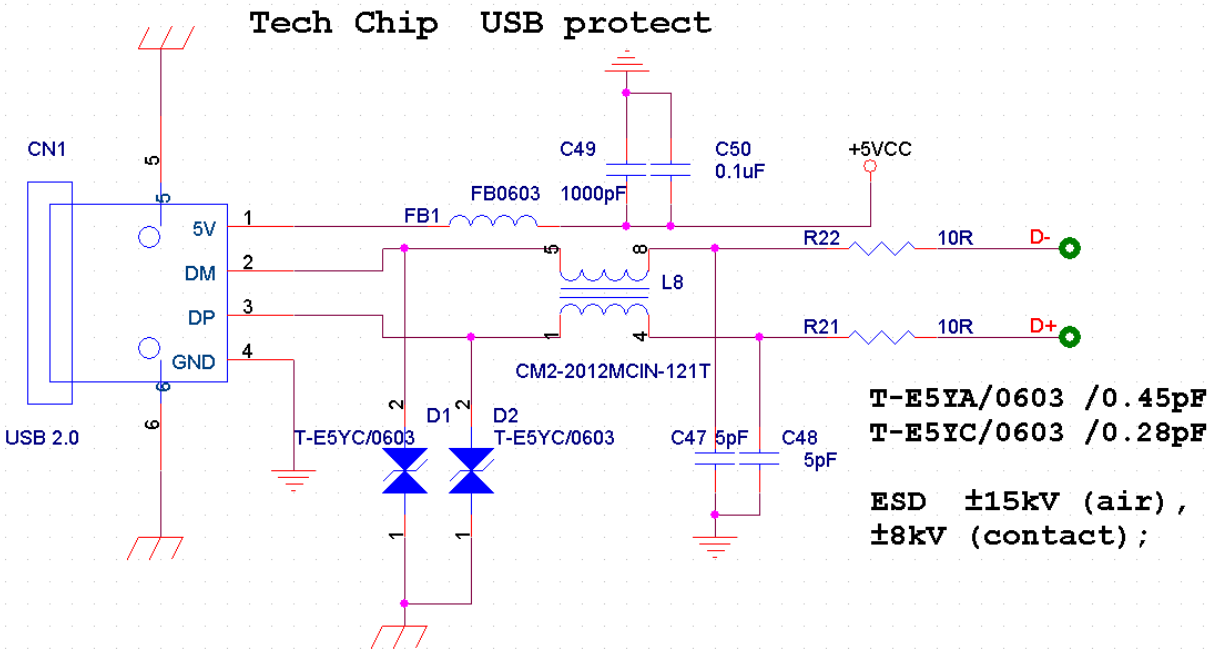
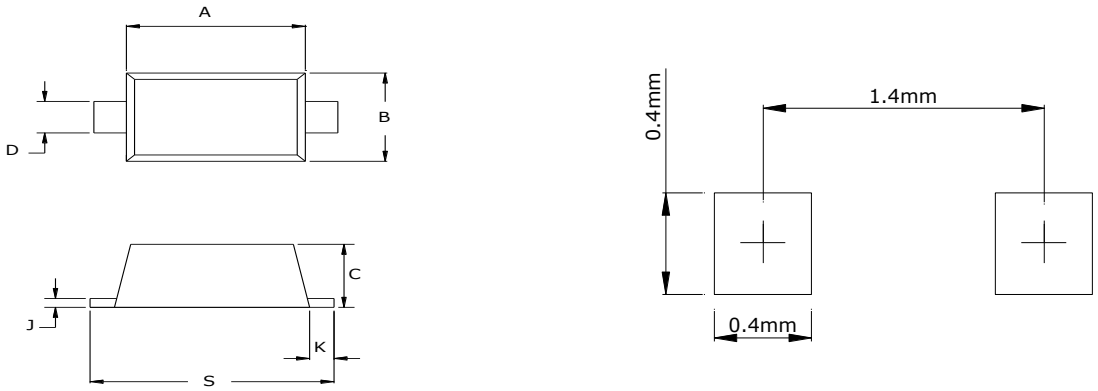


Package information

Recommended Pad outline



Package information

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.10	1.30	0.043	0.051
B	0.70	0.90	0.045	0.053
C	0.50	0.70	0.031	0.043
D	0.25	0.35	0.004	0.012
J	0.07	0.20	0.0028	0.0079
K	0.15	0.25	0.006	0.010
S	1.50	1.70	0.059	0.067